

SAC3094QP3

GaAs MMIC Low Noise Amplifier
7~13GHz

Rev 1.0

Features

- Frequency: 7~13GHz
- Gain: 23dB
- Noise Figure: 0.7dB Typ., 1dB Max.
- OP₋₁dB: 14dBm
- Supply Voltage: +3V@20mA, +5V@40mA
- Package Size: 3mm×3mm×1.1mm

Typical Applications

- Radar and ECM
- RF/ Microwave radio
- Military and Space

General Description

SAC3094QP3 is a GaAs MMIC Low Noise Amplifier in QFN surface mount package, which operates between in 7~13GHz.

The amplifier can provide 23dB of gain, 14dBm of output P₋₁dB and 0.7dB noise figure and from a 20mA supply current.

SAC3094QP3 is assembled in a 3mm x 3mm QFN plastic package.

Picture



Electrical Performance 1 (T_A=25°C, V_D=+3V, I_D=20mA, Z₀=50Ω)

| Parameter | Min | Typ. | Max | Units |
|---|------|------|------|-------|
| Frequency Range | 7~13 | | | GHz |
| Gain | 18 | 21 | 25 | dB |
| Gain Flatness | — | ±1 | ±1.5 | dB |
| Input/Output VSWR | — | 1.5 | 2.2 | :1 |
| Noise Figure | — | 0.7 | 1 | dB |
| Reserve Isolation | — | -37 | — | dB |
| Output Power for 1 dB Compression (OP ₋₁ dB) | 5 | 8 | — | dBm |
| Output Third Order Intercept (OIP ₃) | — | 20 | — | dBm |
| Supply Current(I _D) | — | 20 | 30 | mA |

Electrical Performance 1 (T_A=25°C, V_D=+5V, I_D=40mA, Z₀=50Ω)

| Parameter | Min | Typ. | Max | Units |
|---|------|------|------|-------|
| Frequency Range | 7~13 | | | GHz |
| Gain | 19 | 23 | 26 | dB |
| Gain Flatness | — | ±1 | ±1.5 | dB |
| Input/Output VSWR | — | 1.5 | 2.2 | :1 |
| Noise Figure | — | 0.7 | 1 | dB |
| Reserve Isolation | — | -37 | — | dB |
| Output Power for 1 dB Compression (OP ₋₁ dB) | 13 | 15 | — | dBm |
| Output Third Order Intercept (OIP ₃) | — | 28 | — | dBm |
| Supply Current(I _D) | — | 40 | 52 | mA |

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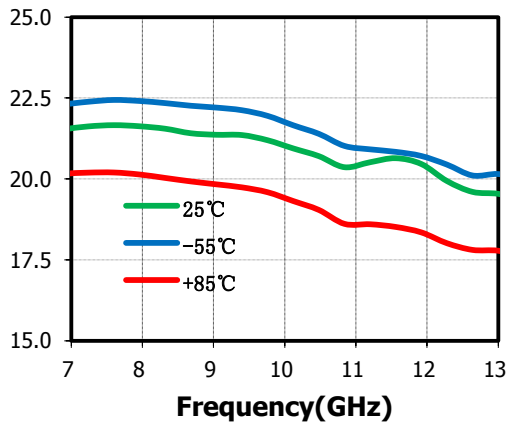
Absolute Maximum Ratings

| | | | |
|---------------------|---------------|-----------------------|--------------|
| Maximum Input Power | +18dBm,CW 30s | Operating Temperature | -55°C~+85°C |
| Channel Temperature | +150°C | Storage Temperature | -65°C~+150°C |
| Supply Voltage | +7V | | |

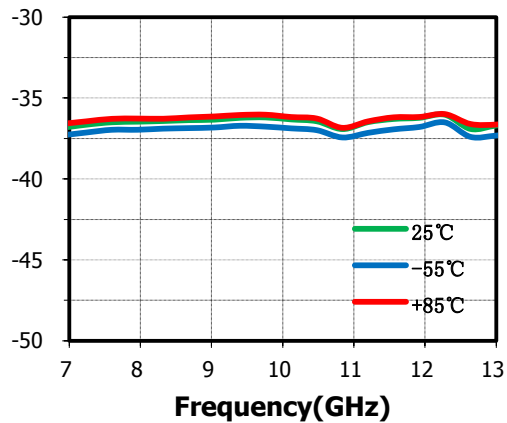
Typical Performance Curve

$V_D=+3V, I_{DQ}=20mA$, The following curves are taken from SAC3094QP3 evaluation board. De-embedding operation has been Implemented.

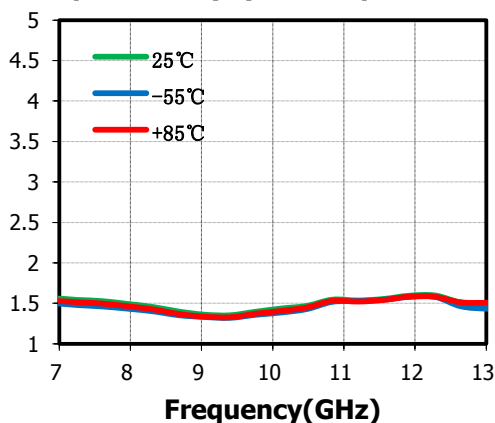
Small Signal Gain(dB) vs.Temperature



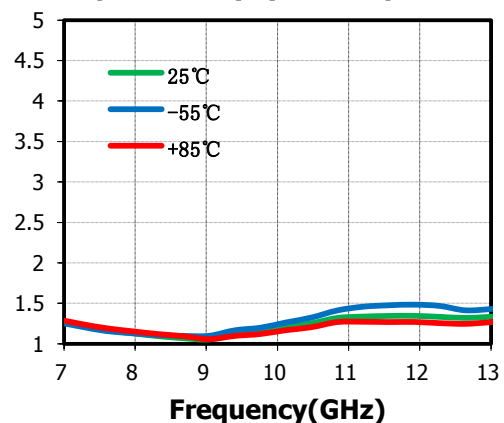
Reverse Isolation(dB) vs.Temperature



Input VSWR(:1) vs.Temperature



Output VSWR(:1) vs.Temperature



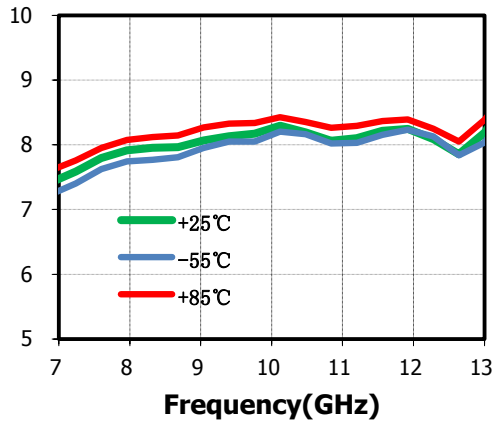
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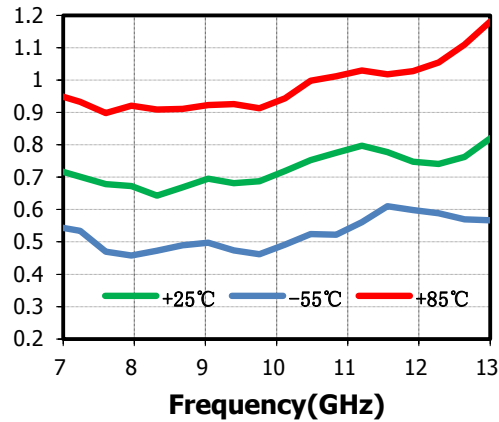
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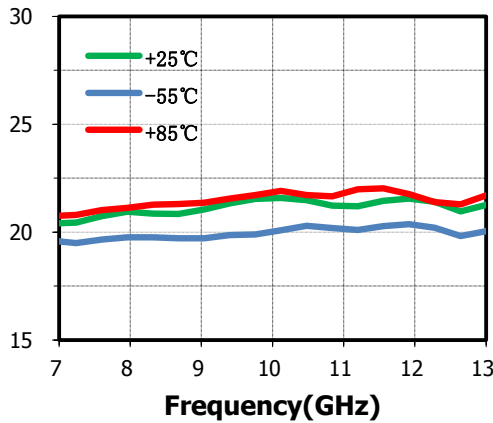
Output P-1dB(dBm) vs.Temperature



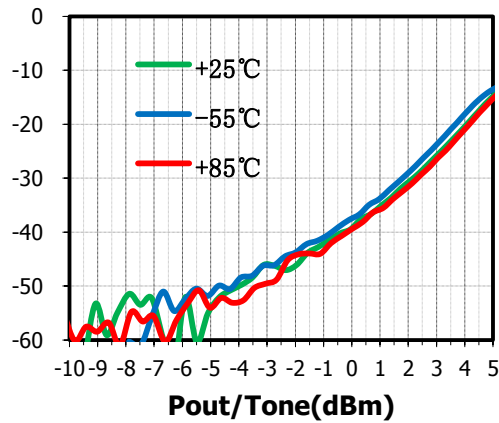
Noise Figure(dB) vs.Temperature



Output IP3(dBm) vs.Temperature

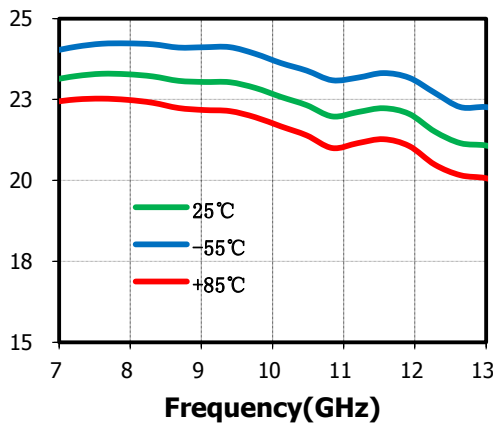


IM3(dBc)vs.Pout/Tone,f=9GHz

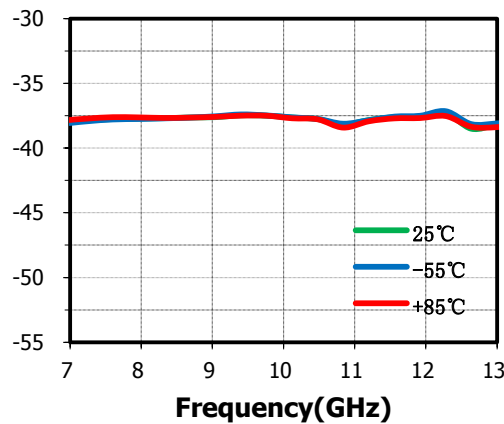


$V_D=+5V, I_{DQ}=40mA$, The following curves are taken from SAC3094QP3 evaluation board. De-embedding operation has been implemented.

Small Signal Gain(dB) vs.Temperature



Reverse Isolation(dB) vs.Temperature



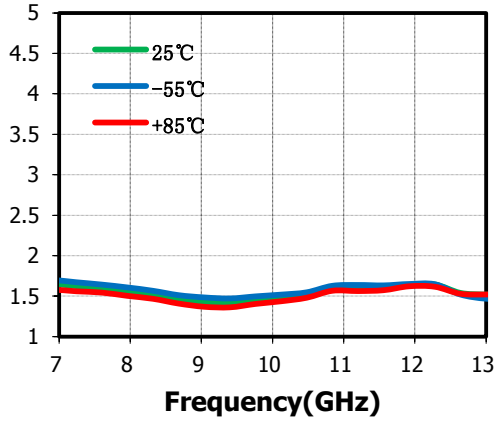
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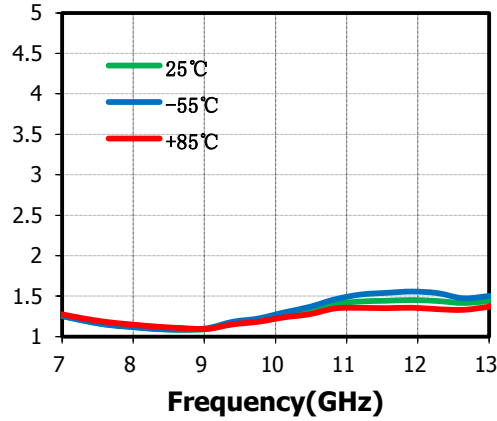
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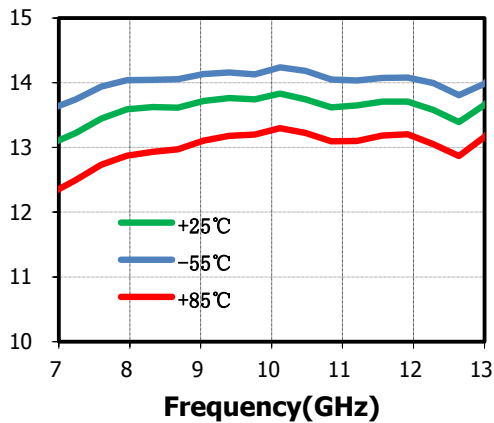
Input VSWR(:1) vs.Temperature



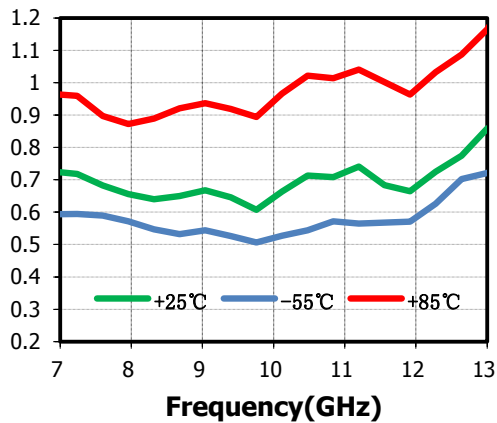
Output VSWR(:1) vs.Temperature



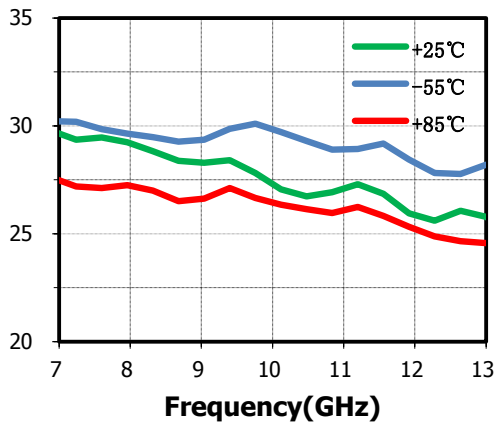
Output P-1dB(dBm) vs.Temperature



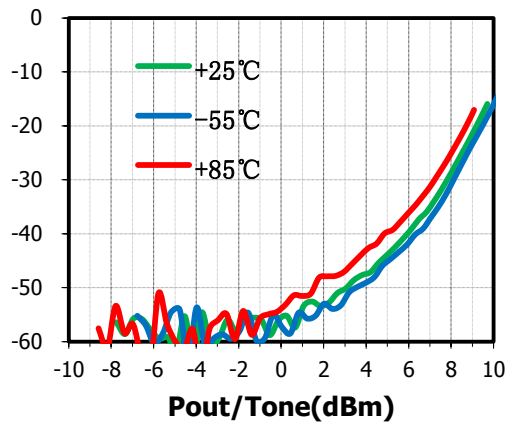
Noise Figure(dB) vs.Temperature



Output IP₃(dBm) vs.Temperature



IM₃(dBc)vs.Pout/Tone,f=9GHz

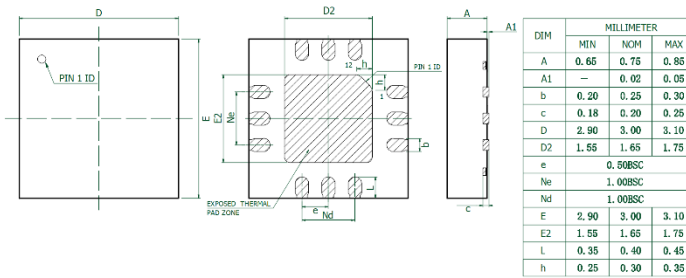


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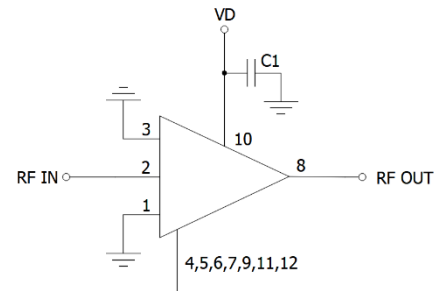
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Outline Drawing



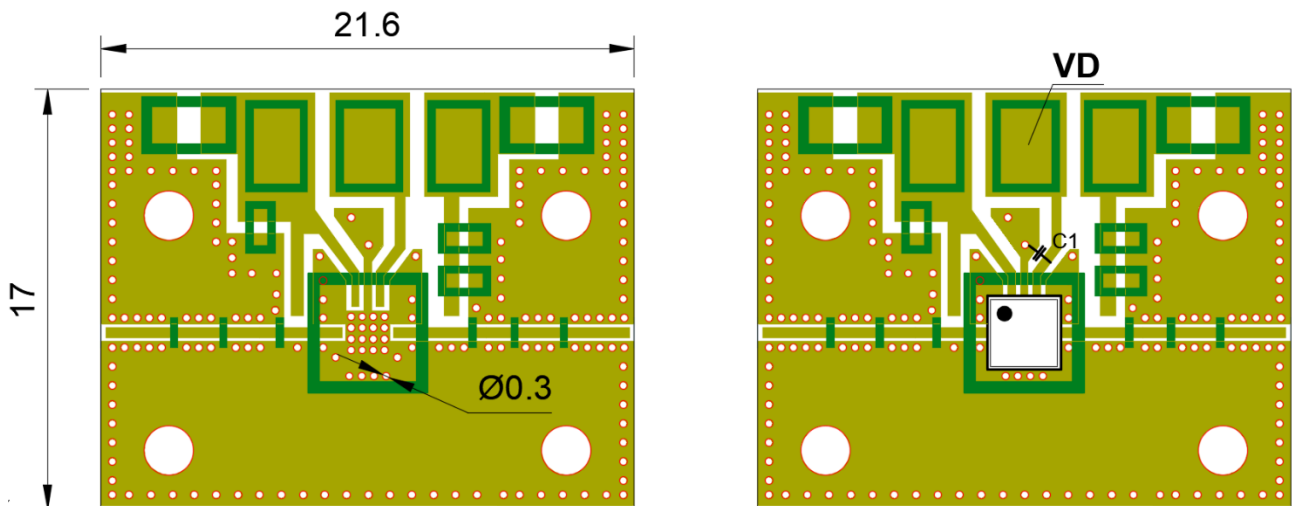
Application Circuit



Pin Function

| Pin No. | Description | Pin No. | Description |
|---------|----------------------|---------|-------------------------|
| 1 | Connect to ground | 7 | Connect to ground |
| 2 | RF input, AC Coupled | 8 | RF output, AC Coupled |
| 3 | Connect to ground | 9 | Connect to ground |
| 4 | Connect to ground | 10 | Drain(VD) |
| 5 | Connect to ground | 11 | NC or Connect to ground |
| 6 | Connect to ground | 12 | NC or Connect to ground |

SAC3094QP3 Evaluation Board



The Evaluation board is a 2-layer board fabricated using Rogers 4350 t=0.254 and using best practices for high frequency RF design. The RF input and RF output traces have a 50 Ω characteristic impedance

Components List

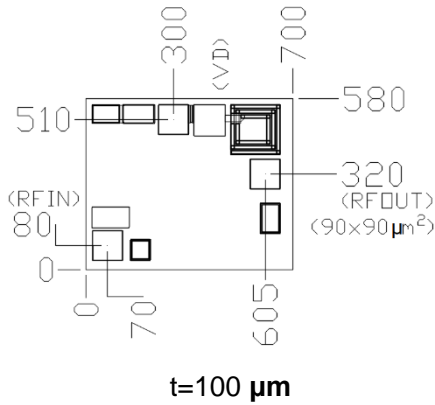
| Reference Des. | Value | Part Number | Manuf. |
|----------------|--------|------------------|--------|
| C1 | 0.01uF | GRM0336R61A103KE | Murata |

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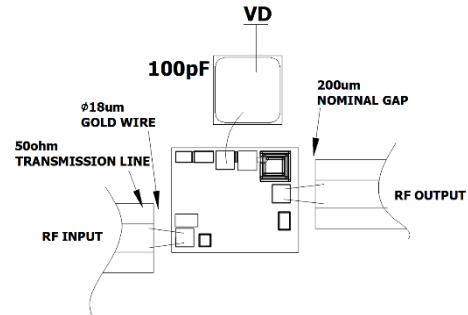
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Die Outline (μm)



Assembly Diagram



Notes

1. The back of chip is RF ground;
2. RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized;
3. Bypass SLCs should be placed as close as possible to the chip;
4. GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test;
5. The MSL level of products is 2a, the storage environment $\leq 30^{\circ} \text{C}/60\% \text{RH}$, The surrounding workshop life is 4 weeks.

Revision History

| Revision | Date | Comment |
|----------|-----------|---------------|
| 1.0 | Feb. 2022 | First Release |